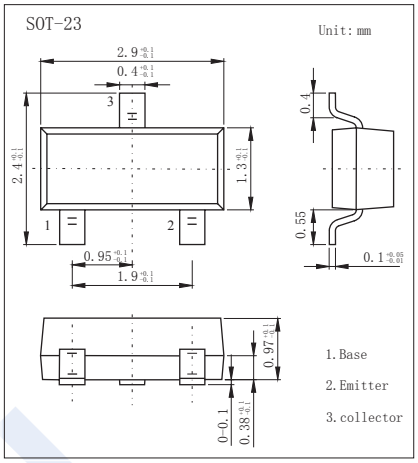
PNP Transistors

KTA1505 (KTA1505S)



■ Features

- Excellent hFE Linearity
- Comlementary to KTC3876/KTC3876S

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-35	V
Collector - Emitter Voltage	V_{CEO}	-30	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-500	mA
Base Current	I_B	-50	
Collector Power Dissipation Tc = 25℃	P_C	150	mW
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 uA, I_E=0	-35			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA, I_B=0	-30			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 uA, I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -35V , I_E=0			-0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA, I_B=-10mA			-0.25	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-100mA, I_B=-10mA			-1.2	
Base - emitter voltage	V_{BE}	V_{CE}= -1V, I_C= -100mA			-1	
DC current gain	h_{FE}	V_{CE}= -1V, I_C= -100mA	70		400	
		V_{CE}= -6V, I_C= -400mA O	25			
		Y	40			
Collector output capacitance	C_{ob}	V_{CB}= -6V, I_E= 0,f=1MHz		13		pF
Transition frequency	f_T	V_{CE}= -6V, I_C= -20mA		200		MHz

■ Classification of $h_{fe(1)}$

Type	KTA1505-O	KTA1505-Y	KTA1505-G
Range	70-140	120-240	200-400
Marking	AZO	AZY	AZG

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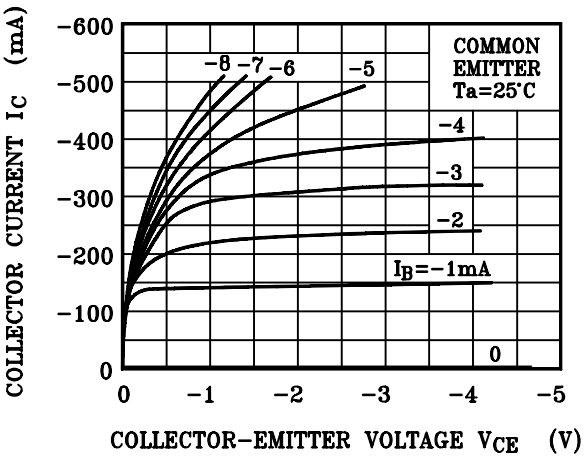
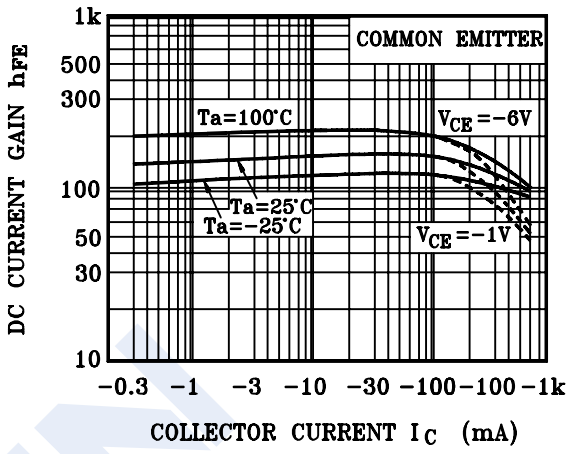
■ Typical Characterisitics

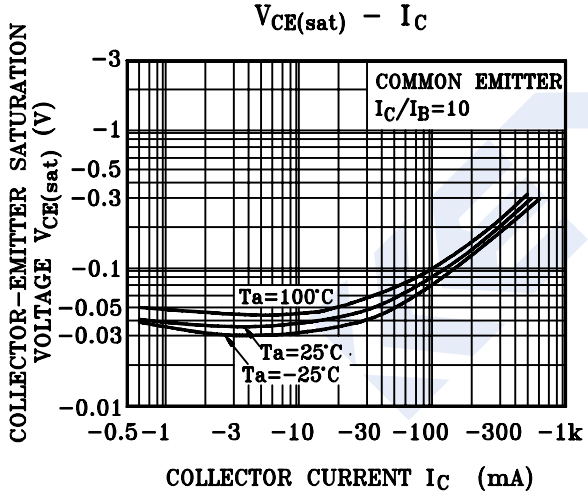
I_C – V_{CE} (LOW VOLTAGE REGION)



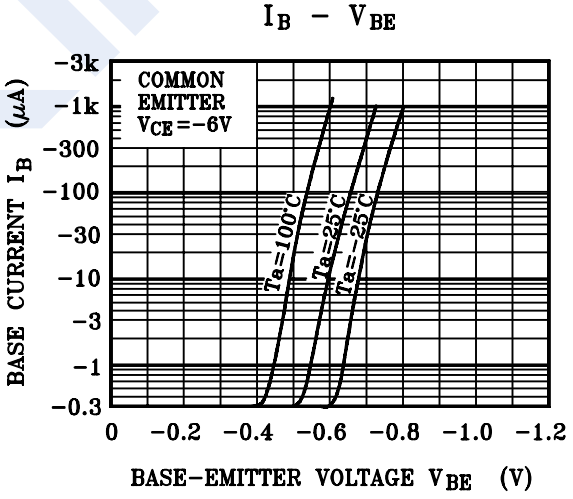
h_{FE} – I_C



$V_{CE(sat)}$ – I_C



I_B – V_{BE}



P_C – Ta